

LibreSilicon process HKUST (NFF)

David Lanzendörfer

August 1, 2019

Abstract

Copyright © 2017 LANCEVILLE TECHNOLOGY GROUP CO., LIMITED. All rights reserved.

This process is licensed under the Libre Silicon public license; you can redistribute it and/or modify it under the terms of the Libre Silicon public license as published by the Libre Silicon alliance, either version 1 of the License, or (at your option) any later version.

This design is distributed in the hope that it will be useful, but WITHOUT ANY WARRANTY; without even the implied warranty of MERCHANTABILITY or FITNESS FOR A PARTICULAR PURPOSE. See the Libre Silicon Public License for more details.

This document is part of the specification of the free silicon manufacturing standard for manufacturing the LibreSilicon standard logic cells¹ and related free technology nodes from the LibreSilicon project.

For this initial revision 0.1 a gate-first approach has been chosen which led to the choice of polysilicon as the gate electrode material because of the simplicity of the gate alignment. For better isolation properties of the transistors and gates in overall a box-isolation approach has been chosen. All of these choices have been made with the future scale down from the recent $1\mu m$ to smaller structure sizes. **This process is for manufacturing $1\mu m$ only!** But further releases which will have been tested with smaller structure sizes can be expected.

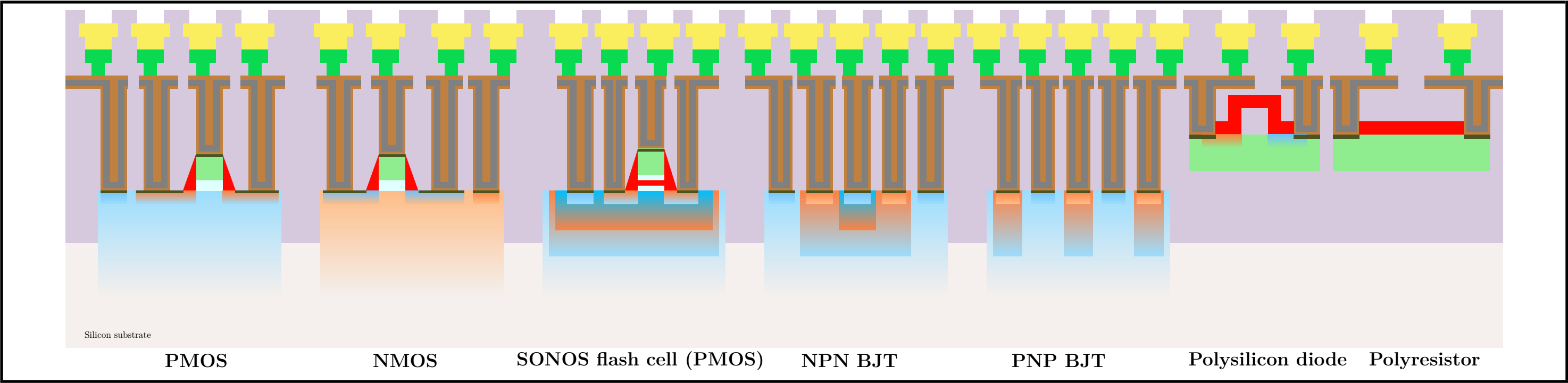
Please see the document with the generic steps² in order to get a detailed description of the different steps.

¹<https://github.com/chipforge/StdCellLib>

²https://download.libresilicon.com/process/v1/process_hightech_steps.pdf

Process Flow of Lanceville Technologies LibreSilicon 1 μm

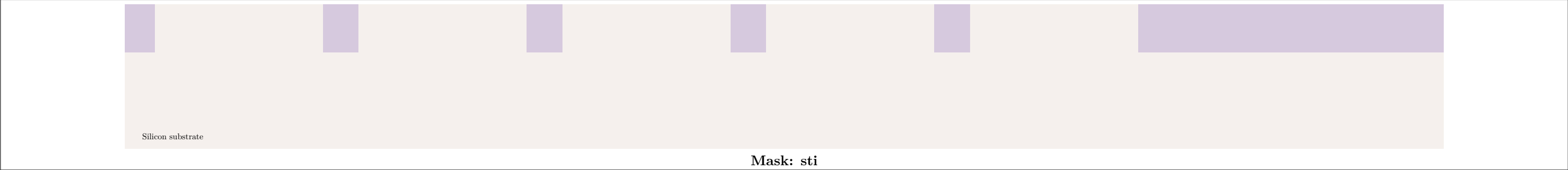
- Project: LibreSilicon 1 μm
- Name: Lanceville Technologies Group
- Substrate: P-Substrate silicon wafer <100>
- Date: August 1, 2019



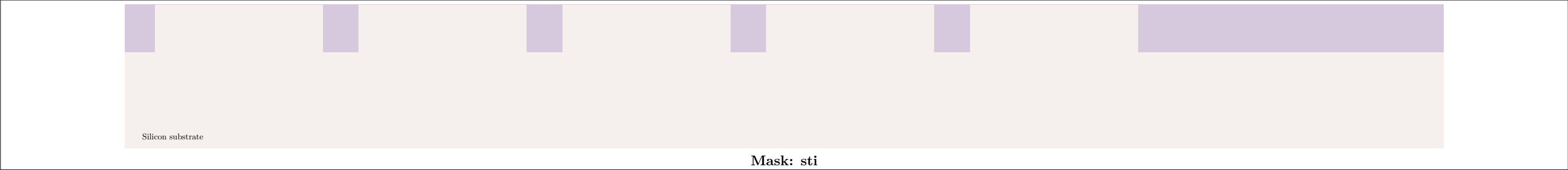
1 Initial alignment mask

Silicon substrate						
Mask: basic						
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	1.1	B1: Sulfuric cleaning (WET-B1)	P2-01000	Clean	Default cleaning	
Clean	1.2	Spin Dryer-B (SRD-B)	P2-01000	Clean	Dry the wafer automatically	
Clean	1.3	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	1.4	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Clean	1.5	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Clean	1.6	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	CF4 Etch	140 seconds
Clean	1.7	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	1.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	1.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	

2 Shallow trench isolation

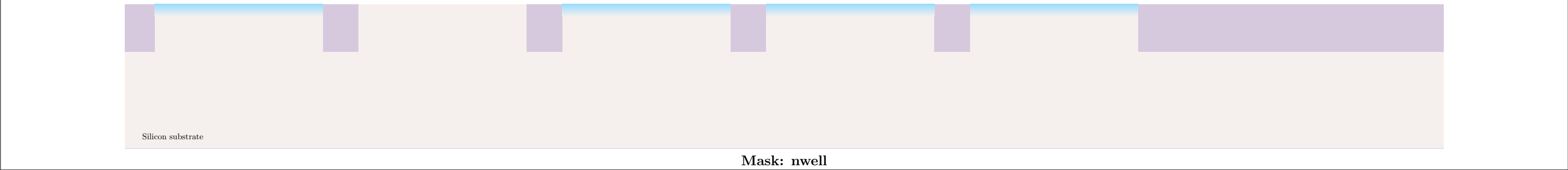


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	2.1	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Initial Cleaning	H2SO4+H2O2, 10mins @ 120°C
Clean	2.2	A2:HF:H2O (1:50) (WET-A2)	P2-01000	Clean	HF dip	1 min
Clean	2.3	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	2.4	Diff. Furnace-D1 Dry Oxidation (Only for gate oxide) (DIF-D1)	P2-01000	Clean	Pad oxide growth	10nm, 15 minutes @ 1000°C in dry environment
Clean	2.5	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	2.6	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	2.7	LPCVD-B2 Nitride/Low-Stress Nitride (CVD-B2)	P2-01000	Clean	CMP end stop deposition, Silicon nitride	100nm
Clean	2.8	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	2.9	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Clean	2.10	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Clean	2.11	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	CHF3 etch	4 minutes
Clean	2.12	DRIE Etcher #1 (DRY-Si-1)	P2-01000	Clean	SMALL001	$2\mu m$ -> 14 cycles
Clean	2.13	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	2.14	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	



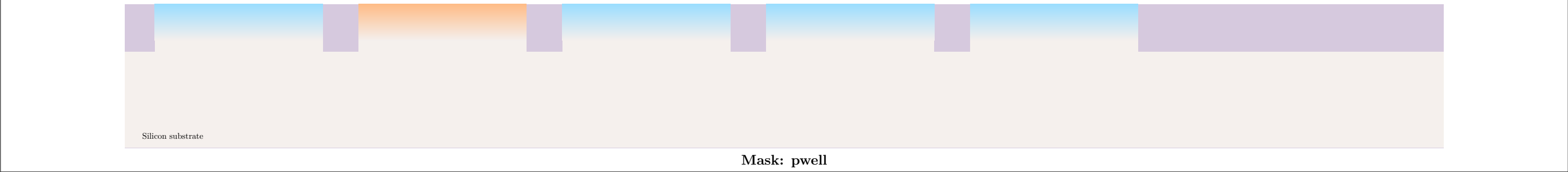
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	2.15	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	
Clean	2.16	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	2.17	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	2.18	LPCVD-B3 LTO (CVD-B3)	P2-01000	Clean	Oxide deposition	2μm LTO
Clean	2.19	Strasbaugh CMP (CMP-1)	P2-10000	Clean	Planarize oxide	10 minutes
Clean	2.20	G1:TMAH (WET-G1)	P2-01000	Clean	Ammonium cleaning	70°C , 10mins
Clean	2.21	C1:Nitride Strip (WET-C1)	P2-01000	Clean	Nitride strip	Remove CMP endstop
Clean	2.22	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	2.23	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	2.24	Diffusion Furnace-A1, anneal/oxidation (DIF-A1)	P2-01000	Clean	Densify LTO	30 minutes @ 850°C in inert atmosphere
Clean	2.25	A2:HF:H2O (1:50) (WET-A2)	P2-01000	Clean	Pad oxide removal/smoothing	3 minutes
Clean	2.26	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	

3 N-well



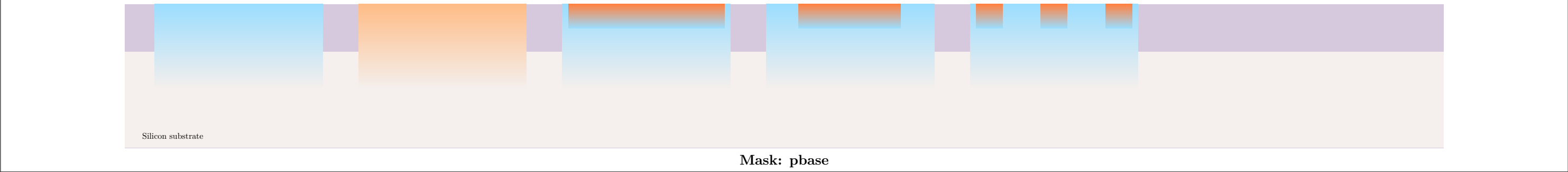
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	3.1	B1: Sulfuric cleaning (WET-B1)	P2-01000	Clean	Default cleaning	
Clean	3.2	Spin Dryer-B (SRD-B)	P2-01000	Clean	Dry the wafer automatically	
Clean	3.3	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	FH 6400L: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	3.4	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$340mJcm^2$
Clean	3.5	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30min
Clean	3.6	CF-3000 Implanter (IMP-3000)	P2-01000	Clean Semi clean	Phorphorus implant	$2.33 \times 10^{12}cm^{-2}@70keV$
Clean	3.7	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	3.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	3.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	

4 P-well



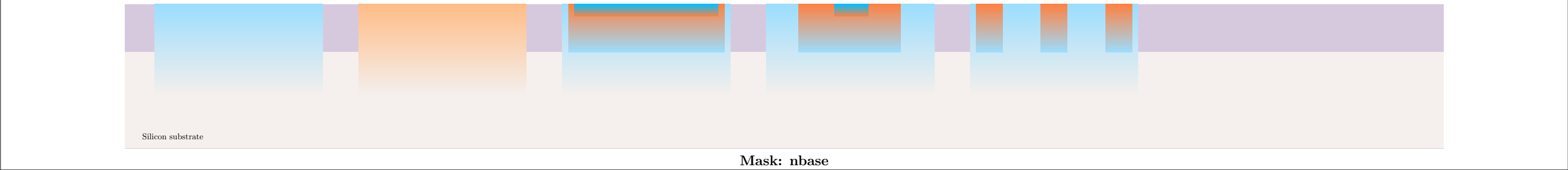
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	4.1	B1: Sulfuric cleaning (WET-B1)	P2-01000	Clean	Default cleaning	
Clean	4.2	Spin Dryer-B (SRD-B)	P2-01000	Clean	Dry the wafer automatically	
Clean	4.3	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	FH 6400L: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	4.4	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$340mJcm^2$
Clean	4.5	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30min
Clean	4.6	CF-3000 Implanter (IMP-3000)	P2-01000	Clean Semi clean	Boron implant	$1.93 \times 10^{12}cm^{-2}@40keV$
Clean	4.7	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	4.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	4.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	
Clean	4.10	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	4.11	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	4.12	Diffusion Furnace-A1, anneal/oxidation (DIF-A1)	P2-01000	Clean	Drive in	2 hours @ 1050°C in inert (N_2) environment

5 P-Base



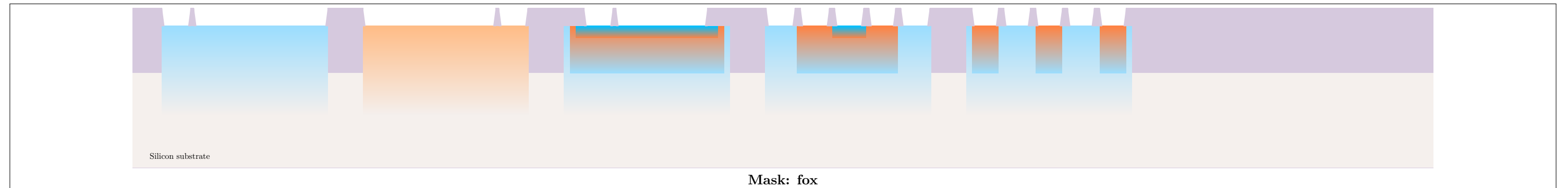
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	5.1	B1: Sulfuric cleaning (WET-B1)	P2-01000	Clean	Default cleaning	
Clean	5.2	Spin Dryer-B (SRD-B)	P2-01000	Clean	Dry the wafer automatically	
Clean	5.3	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	FH 6400L: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	5.4	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$340mJcm^2$
Clean	5.5	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30min
Clean	5.6	CF-3000 Implanter (IMP-3000)	P2-01000	Clean Semi clean	Boron implant	$1.93 \times 10^{12}cm^{-2}@40keV$
Clean	5.7	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	5.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	5.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	
Clean	5.10	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	5.11	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	5.12	Diffusion Furnace-A1, anneal/oxidation (DIF-A1)	P2-01000	Clean	Drive in	1 hour @ 1050°C in inert (N_2) environment

6 N-Base

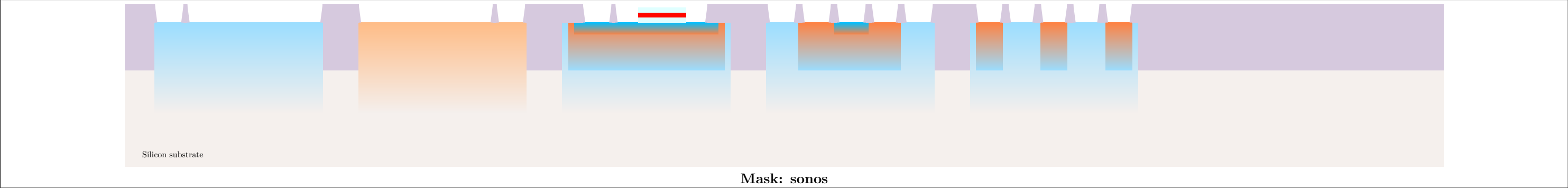


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	6.1	B1: Sulfuric cleaning (WET-B1)	P2-01000	Clean	Default cleaning	
Clean	6.2	Spin Dryer-B (SRD-B)	P2-01000	Clean	Dry the wafer automatically	
Clean	6.3	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	FH 6400L: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	6.4	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$340mJcm^2$
Clean	6.5	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30min
Clean	6.6	CF-3000 Implanter (IMP-3000)	P2-01000	Clean Semi clean	Phorphorus implant	$2.33 \times 10^{12}cm^{-2}@70keV$
Clean	6.7	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	6.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	6.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	
Clean	6.10	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	6.11	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	6.12	Diffusion Furnace-A1, anneal/oxidation (DIF-A1)	P2-01000	Clean	Drive in	30 minutes @ 1050°C in inert (N_2) environment

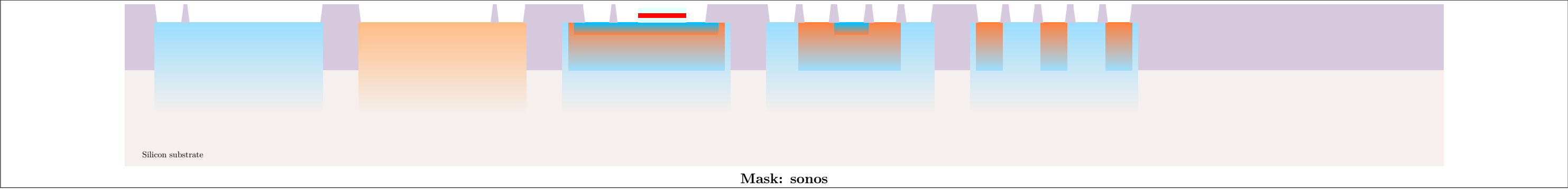
7 Field oxide



Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	7.1	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	7.2	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	7.3	LPCVD-B3 LTO (CVD-B3)	P2-01000	Clean	Oxide deposition	200nm LTO
Clean	7.4	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	7.5	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Clean	7.6	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Clean	7.7	AOE Etcher (DRY-AOE)	P2-01000	Clean	Etch oxide FOX openings	Etch through 200nm
Clean	7.8	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	7.9	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	7.10	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	

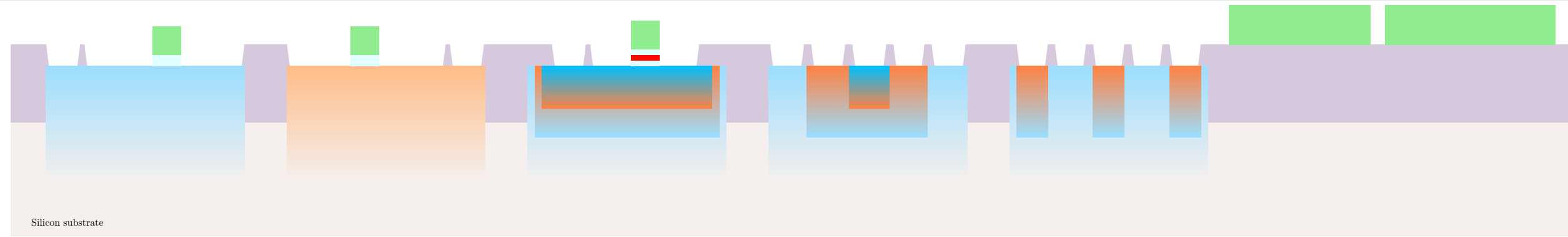


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	8.1	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	8.2	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	8.3	LPCVD-B3 LTO (CVD-B3)	P2-01000	Clean	Lower gate oxide growth	5nm
Clean	8.4	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	8.5	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	8.6	LPCVD-B2 Nitride/Low-Stress Nitride (CVD-B2)	P2-01000	Clean	Charge carrying nitride growth	10nm
Clean	8.7	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	8.8	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	8.9	LPCVD-B3 LTO (CVD-B3)	P2-01000	Clean	Lower gate oxide growth	5nm
Clean	8.10	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	8.11	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Clean	8.12	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Clean	8.13	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	Nitride etch	30 seconds (50nm, 100nm/min)
Clean	8.14	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	



Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	8.15	E4:Resist strip (WET-E4)	P2-01000	CleanSemi clean	Resist strip	
Clean	8.16	Spin Dryer-E (SRD-E)	P2-01000	CleanSemi clean	Dry the wafer automatically	

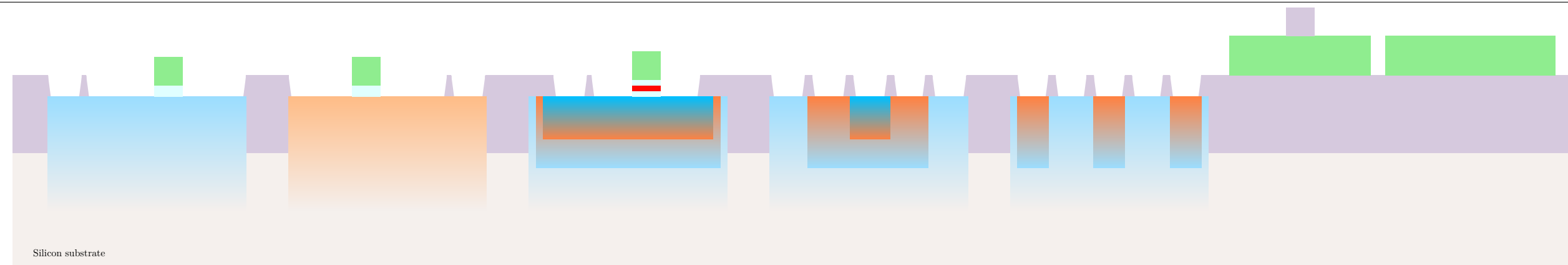
9 Gate



Mask: poly

Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	9.1	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	9.2	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	9.3	Diff. Furnace-D1 Dry Oxidation (Only for gate oxide) (DIF-D1)	P2-01000	Clean	Gate oxide growth	40nm, 33 minutes 14 seconds @ 1050°C in dry environment
Clean	9.4	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	9.5	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	9.6	LPCVD-A3: Amor-Si/Poly (CVD-A3)	P2-01000	Clean	Gate electrode growth	250nm of poly silicon
Clean	9.7	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	9.8	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Clean	9.9	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Clean	9.10	Poly etcher (DRY-Poly)	P2-01000	Clean Semi clean	Poly silicon etch	HBr only, 2 minutes
Clean	9.11	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	9.12	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	9.13	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	

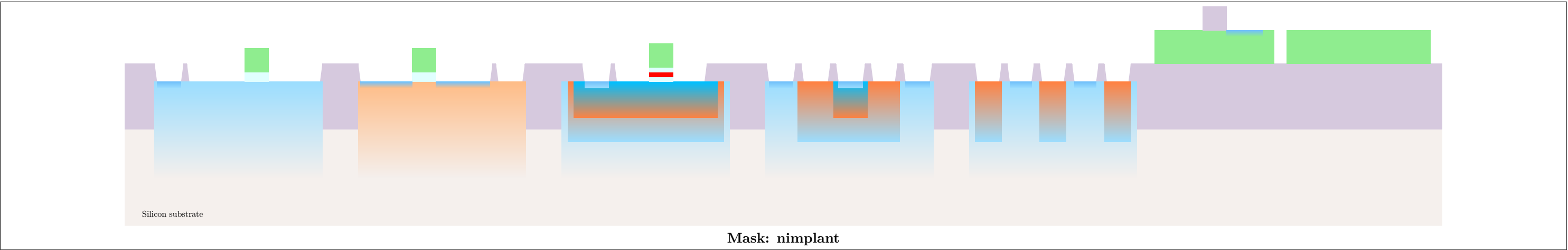
10 Implant stop



Mask: implantstop

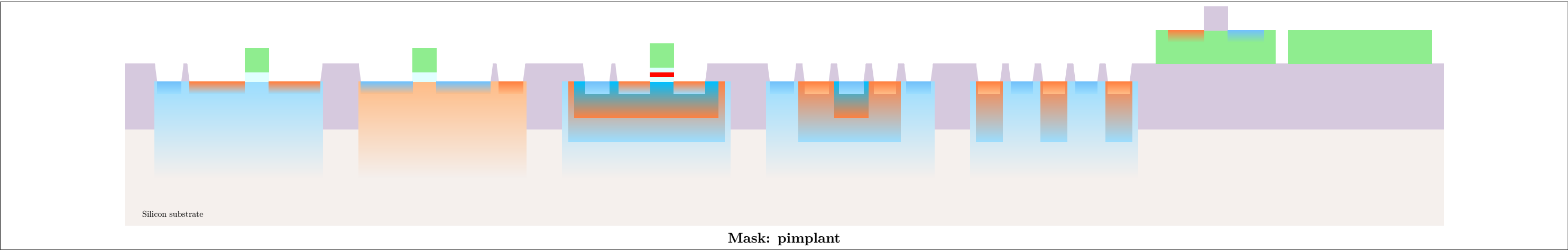
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	10.1	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	10.2	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	10.3	LPCVD-B3 LTO (CVD-B3)	P2-01000	Clean	Oxide deposition	200nm LTO
Clean	10.4	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	10.5	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Clean	10.6	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Clean	10.7	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	CHF3 etch	300 seconds
Clean	10.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Sulfuric resist strip	H2SO4+H2O2, 120°C , 10mins
Clean	10.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	

11 N+ implant



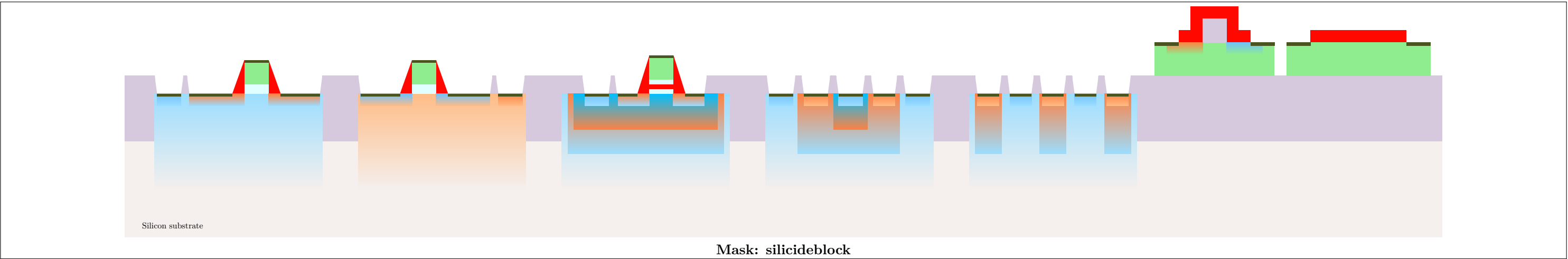
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	11.1	B1: Sulfuric cleaning (WET-B1)	P2-01000	Clean	Default cleaning	
Clean	11.2	Spin Dryer-B (SRD-B)	P2-01000	Clean	Dry the wafer automatically	
Clean	11.3	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	FH 6400L: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	11.4	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$340mJcm^2$
Clean	11.5	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30min
Clean	11.6	CF-3000 Implanter (IMP-3000)	P2-01000	Clean Semi clean	Phorphorus implant	$2.5 \times 10^{12}cm^{-2}$ @ 30keV
Clean	11.7	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	11.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	11.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	

12 P+ implant



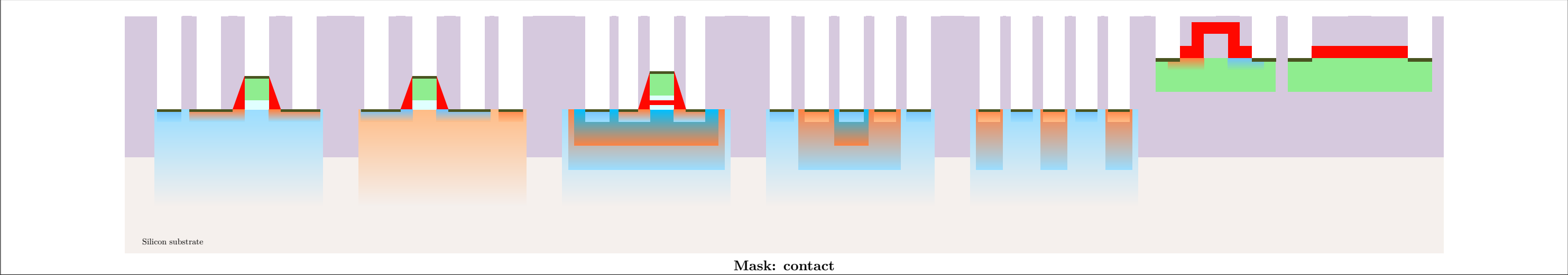
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	12.1	B1: Sulfuric cleaning (WET-B1)	P2-01000	Clean	Default cleaning	
Clean	12.2	Spin Dryer-B (SRD-B)	P2-01000	Clean	Dry the wafer automatically	
Clean	12.3	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	FH 6400L: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	12.4	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$340mJcm^2$
Clean	12.5	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30min
Clean	12.6	CF-3000 Implanter (IMP-3000)	P2-01000	Clean Semi clean	Boron implant	$2.5 \times 10^{12}cm^{-2}$ @ 20keV
Clean	12.7	PS210 Asher (DRY-PR-1)	P2-01000	Clean	Resist strip	
Clean	12.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Resist strip	
Clean	12.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	
Clean	12.10	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	12.11	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	12.12	Diffusion Furnace-A1, anneal/oxidation (DIF-A1)	P2-01000	Clean	Drive in	30 minutes @ 900°C , drive in + dry oxidation

13 Silicification



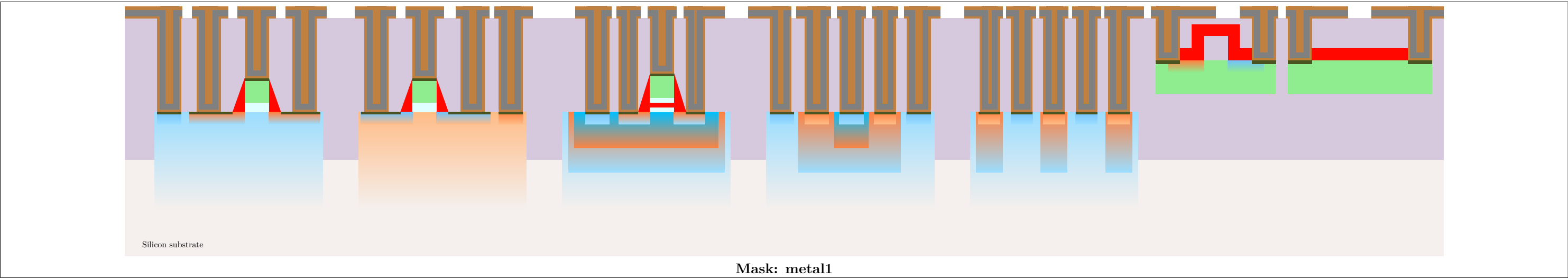
Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Clean	13.1	A3:Sulfuric cleaning (WET-A3)	P2-01000	Clean	Default cleaning	
Clean	13.2	Spin Dryer-A (SRD-A)	P2-01000	Clean	Dry the wafer automatically	
Clean	13.3	LPCVD-B2 Nitride/Low-Stress Nitride (CVD-B2)	P2-01000	Clean	Spacer nitride	50 nm
Clean	13.4	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Clean	13.5	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Clean	13.6	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Clean	13.7	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	Anisotropic nitride etch	120 seconds
Clean	13.8	E4:Resist strip (WET-E4)	P2-01000	Clean Semi clean	Sulfuric resist strip	H2SO4+H2O2, 120°C , 10mins
Clean	13.9	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	
Semi clean	13.10	NSC3000 Sputter (SPT-NSC3000)	P2-01000	Semi clean	Deposit Titanium	50nm
Semi clean	13.11	AG610 RTP (DIF-R2)	P2-01000	Semi clean	Reaction phase	30 seconds @ 800°C , Argon atmosphere
Semi clean	13.12	E2: General purpose (WET-E2)	P2-01000	Semi clean	Remove unreacted Titanium	RCA @ room temperature, 2 minutes
Semi clean	13.13	Spin Dryer-E (SRD-E)	P2-01000	Clean Semi clean	Dry the wafer automatically	

14 Contact

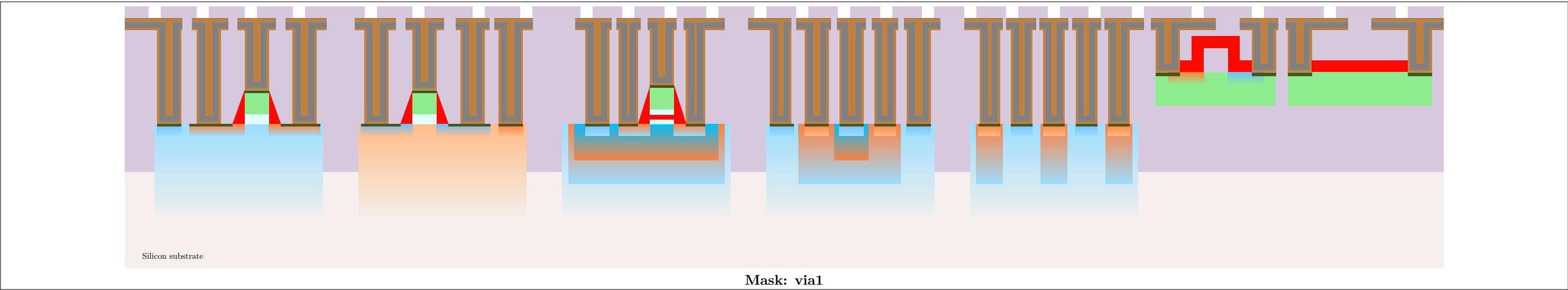


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Semi clean	14.1	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	14.2	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Pad oxide deposition	100nm
Semi clean	14.3	310PC PECVD (CVD-P1)	P2-01000	Semi clean	CMP end stop deposition, Silicon nitride	100nm
Semi clean	14.4	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	14.5	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Oxide deposition	1 μ m
Semi clean	14.6	Buehler Polisher #1 (CMP-4)	Rm. 2227	Semi clean	Planarize oxide	1 minute
Semi clean	14.7	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm (\approx 1.5 μ m), soft bake: 110°C 1min
Semi clean	14.8	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	280mJcm ²
Semi clean	14.9	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Semi clean	14.10	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	CHF3 etch	180 seconds
Semi clean	14.11	Y1:MS2001 Resist strip (WET-Y1)	P2-00100	Semi clean	Resist strip	10mins
Semi clean	14.12	Spin Dryer-Y (SRD-Y)	P2-00100	Semi clean	Spin dry	

15 Metal 1

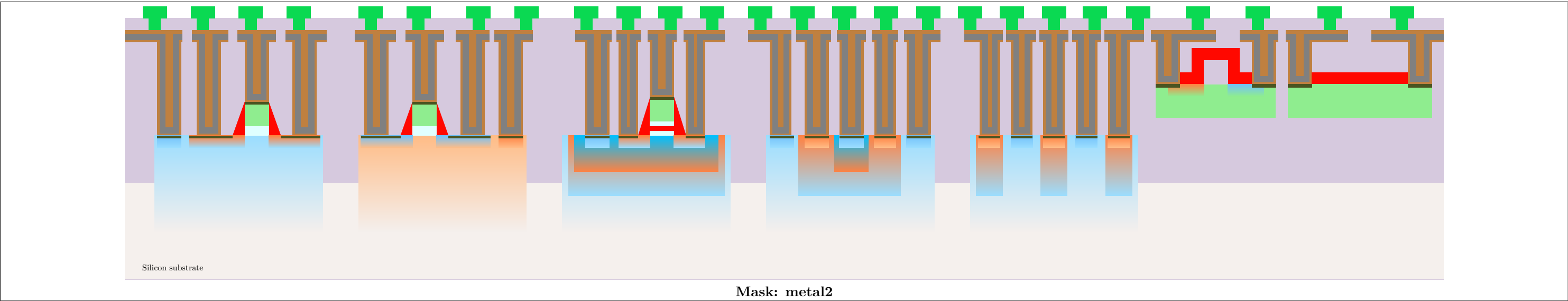


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Semi clean	15.1	NSC3000 Sputter (SPT-NSC3000)	P2-01000	Semi clean	Nickel diffusion barrier + Deposit Aluminum + Nickel finish	Nickel (roughly 50nm) + Aluminum (roughly 100nm) + Nickel (roughly 50nm)
Semi clean	15.2	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Semi clean	15.3	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Semi clean	15.4	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Semi clean	15.5	AST Metal Etcher (DRY-Metal-1)	P2-01000	Semi clean	Wire formation	200 nm
Semi clean	15.6	Y1:MS2001 Resist strip (WET-Y1)	P2-00100	Semi clean	Resist strip	10mins
Semi clean	15.7	Spin Dryer-Y (SRD-Y)	P2-00100	Semi clean	Spin dry	

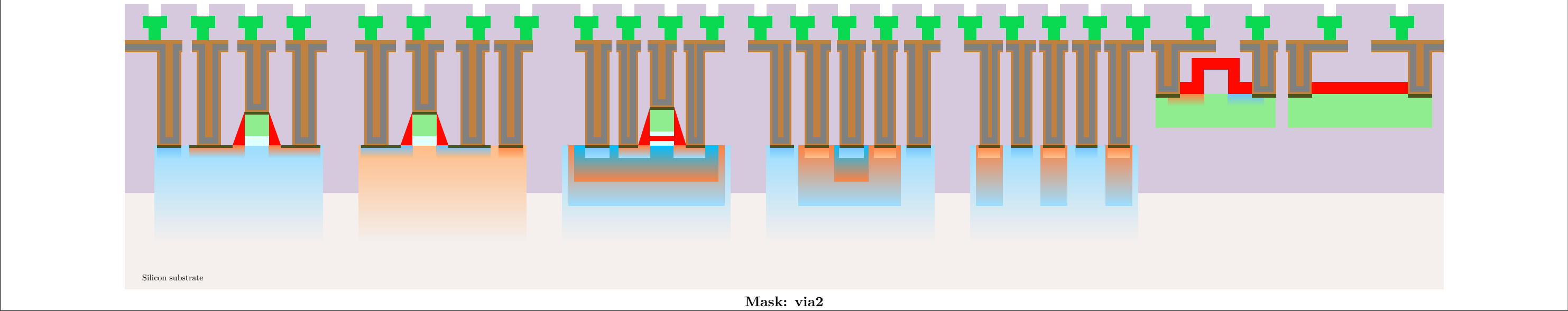


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Semi clean	16.1	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	16.2	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Pad oxide deposition	100nm
Semi clean	16.3	310PC PECVD (CVD-P1)	P2-01000	Semi clean	CMP end stop deposition, Silicon nitride	100nm
Semi clean	16.4	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	16.5	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Oxide deposition	1μm
Semi clean	16.6	Buehler Polisher #1 (CMP-4)	Rm. 2227	Semi clean	Planarize oxide	1 minute
Semi clean	16.7	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm (≈1.5μm), soft bake: 110°C 1min
Semi clean	16.8	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	280mJcm ²
Semi clean	16.9	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Semi clean	16.10	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	CHF3 etch	180 seconds
Semi clean	16.11	Y1:MS2001 Resist strip (WET-Y1)	P2-00100	Semi clean	Resist strip	10mins
Semi clean	16.12	Spin Dryer-Y (SRD-Y)	P2-00100	Semi clean	Spin dry	

17 Metal 2

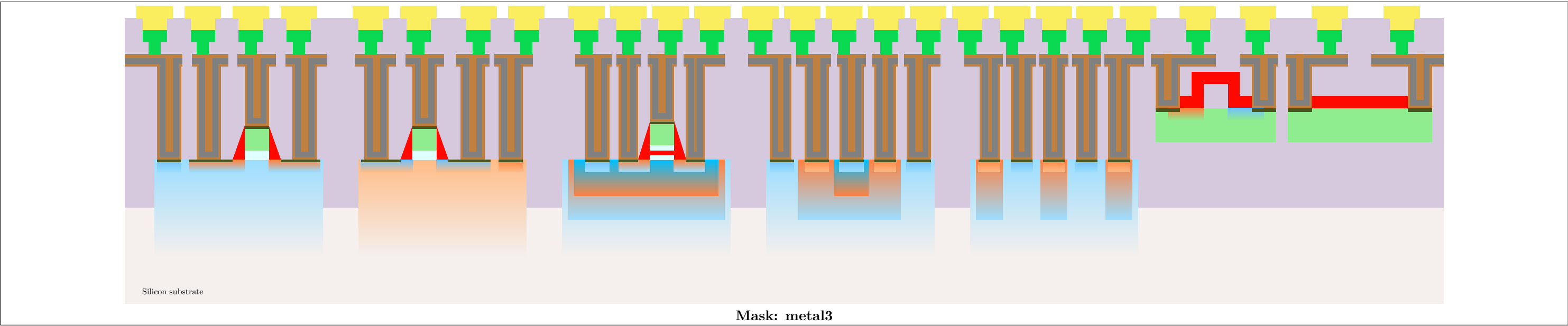


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Semi clean	17.1	NSC3000 Sputter (SPT-NSC3000)	P2-01000	Semi clean	Deposit Aluminum + Nickel finish	Aluminum (roughly 100nm) + Nickel (roughly 50nm)
Semi clean	17.2	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Semi clean	17.3	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Semi clean	17.4	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Semi clean	17.5	AST Metal Etcher (DRY-Metal-1)	P2-01000	Semi clean	Wire formation	150 nm
Semi clean	17.6	Y1:MS2001 Resist strip (WET-Y1)	P2-00100	Semi clean	Resist strip	10mins
Semi clean	17.7	Spin Dryer-Y (SRD-Y)	P2-00100	Semi clean	Spin dry	

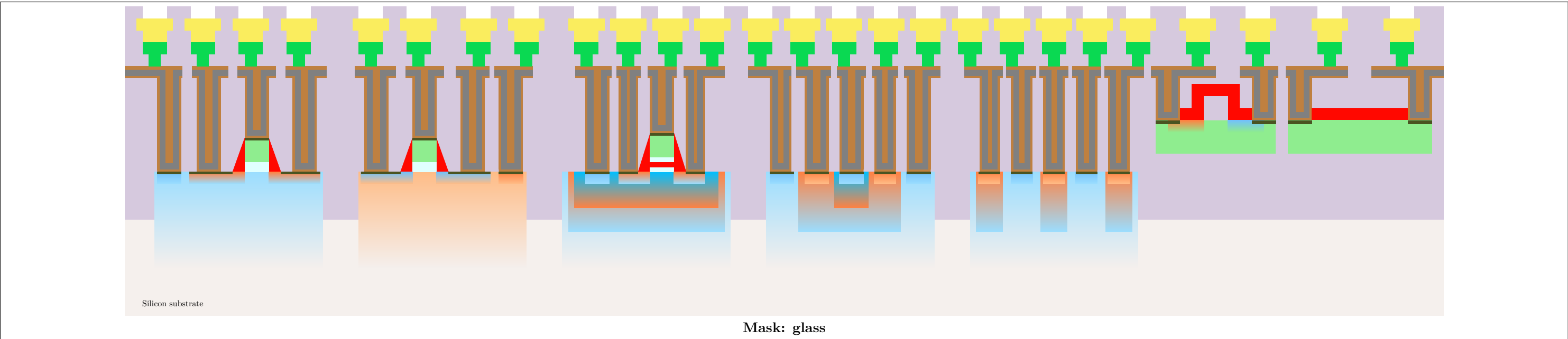


Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Semi clean	18.1	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	18.2	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Pad oxide deposition	100nm
Semi clean	18.3	310PC PECVD (CVD-P1)	P2-01000	Semi clean	CMP end stop deposition, Silicon nitride	100nm
Semi clean	18.4	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	18.5	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Oxide deposition	1μm
Semi clean	18.6	Buehler Polisher #1 (CMP-4)	Rm. 2227	Semi clean	Planarize oxide	1 minute
Semi clean	18.7	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm (≈1.5μm), soft bake: 110°C 1min
Semi clean	18.8	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	280mJcm ²
Semi clean	18.9	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Semi clean	18.10	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	CHF3 etch	180 seconds
Semi clean	18.11	Y1:MS2001 Resist strip (WET-Y1)	P2-00100	Semi clean	Resist strip	10mins
Semi clean	18.12	Spin Dryer-Y (SRD-Y)	P2-00100	Semi clean	Spin dry	

19 Metal 3



Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Semi clean	19.1	NSC3000 Sputter (SPT-NSC3000)	P2-01000	Semi clean	Deposit Aluminum + Nickel finish	Aluminum (roughly 100nm) + Nickel (roughly 50nm)
Semi clean	19.2	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm ($\approx 1.5\mu m$), soft bake: 110°C 1min
Semi clean	19.3	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	$280mJcm^2$
Semi clean	19.4	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Semi clean	19.5	AST Metal Etcher (DRY-Metal-1)	P2-01000	Semi clean	Wire formation	150 nm
Semi clean	19.6	Y1:MS2001 Resist strip (WET-Y1)	P2-00100	Semi clean	Resist strip	10mins
Semi clean	19.7	Spin Dryer-Y (SRD-Y)	P2-00100	Semi clean	Spin dry	



Wafer Cleanliness	Step Number	Equipment	Location	Cleanliness	Process	Requirements
Semi clean	20.1	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	20.2	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Pad oxide deposition	100nm
Semi clean	20.3	310PC PECVD (CVD-P1)	P2-01000	Semi clean	CMP end stop deposition, Silicon nitride	100nm
Semi clean	20.4	D1: Dump rinse (WET-D-DR)	P2-01000	Semi clean	Wafer cleaning	
Semi clean	20.5	LPCVD-F4 LTO/PSG (CVD-F4)	P2-01000	Semi clean	Oxide deposition	1μm
Semi clean	20.6	Buehler Polisher #1 (CMP-4)	Rm. 2227	Semi clean	Planarize oxide	1 minute
Semi clean	20.7	SVG Coater Track (PHT-T1)	P2-00100	Clean Semi clean	HMDS, PR coating, soft bake	HPR 504: 3krpm (≈1.5μm), soft bake: 110°C 1min
Semi clean	20.8	ASML Stepper (PHT-S1)	P2-00100	Clean Semi clean	Exposure of the layer	280mJcm ²
Semi clean	20.9	SVG Developer Track (PHT-T2)	P2-00100	Clean Semi clean	Develop, Hard bake	FHD-5, 1min; hard bake: 120°C , 30 min
Semi clean	20.10	NFF RIE Etcher (DRY-RIE-2)	P2-01000	Clean Semi clean	CHF3 etch	180 seconds
Semi clean	20.11	Y1:MS2001 Resist strip (WET-Y1)	P2-00100	Semi clean	Resist strip	10mins
Semi clean	20.12	Spin Dryer-Y (SRD-Y)	P2-00100	Semi clean	Spin dry	

